GSMBT2907A

PNP EPITAXIAL PLANAR TRANSISTOR

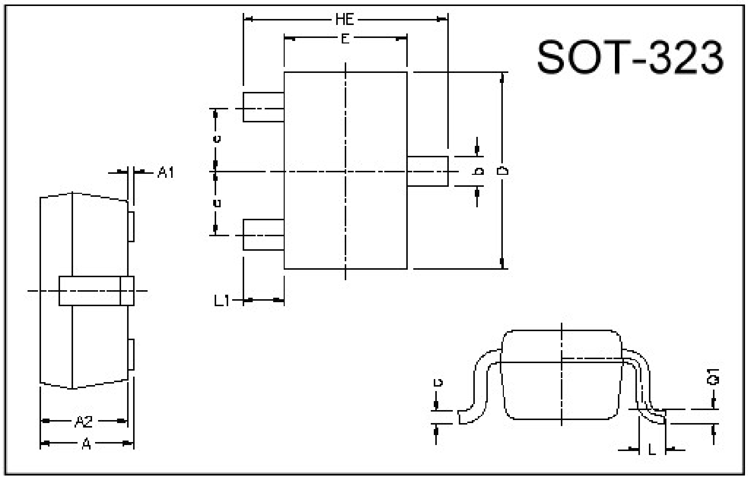
Description

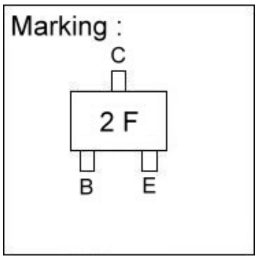
The GSMBT2907A is designed for general purpose amplifier and high speed, medium-power switching applications.

Features

- Low collector saturation voltage
- High speed switching
- For complementary use with NPN type GSMBT2222A

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

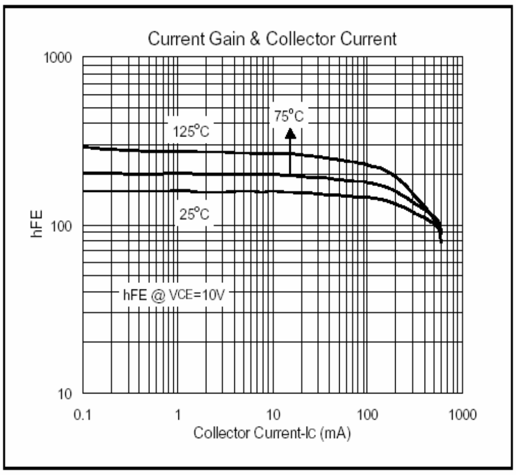
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage at Ta=25℃	VCBO	-60	V
Collector to Emitter Voltage at Ta=25℃	VCEO	-60	V
Emitter to Base Voltage at Ta=25℃	VEBO	-5	V
Collector Current at Ta=25℃	IC	-600	mA
Total Power Dissipation at Ta=25℃	PD	225	mW

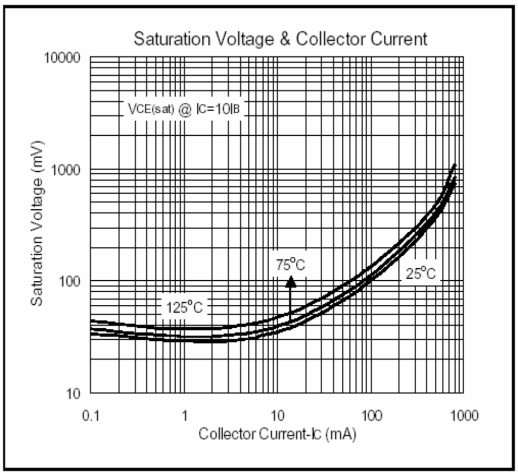
Characteristics at Ta = 25℃

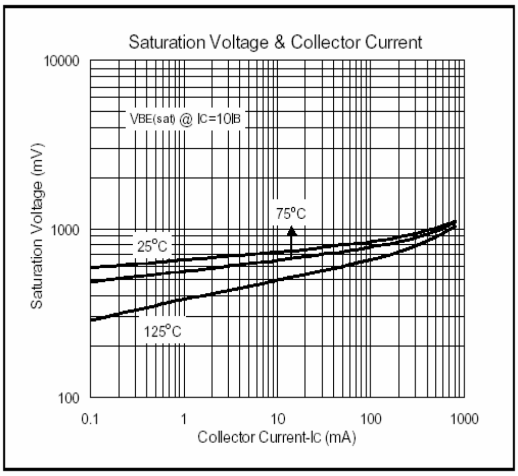
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-60	-	-	V	IC=-10uA
BVCEO	-60	-	-	V	IC=-10mA
BVEBO	-5	-	-	V	IE=-10uA
ICBO	-	-	-10	nA	VCE=-50V
ICEX	-	-	-50	nA	VCE=-30V, VBE=-0.5V
*VCE(sat)1	-	-0.2	-0.4	V	IC=-150mA, IB=-15mA
*VCE(sat)2	-	-0.5	-1.6	V	IC=-500mA, IB=-50mA
*VBE(sat)1	-	-	-1.3	mV	IC=-150mA, IB=-15mA
*VBE(sat)2	-	-	-2.6	V	IC=-500mA, IB=-50mA
*hFE1	75	-	-		VCE=-10V, IC=-0.1mA
*hFE2	100	-	-		VCE=-10V, IC=-1mA
*hFE3	100	-	-		VCE=-10V, IC=-10mA
*hFE4	100	180	300		VCE=-10V, IC=-150mA
*hFE5	50	-	-		VCE=-10V, IC=-500mA
fT	200	-	-	MHz	VCE=-20V, IC=-50mA, f=100MHz
Cob	-	-	8.0	pF	VCE=-10V, f=1MHz

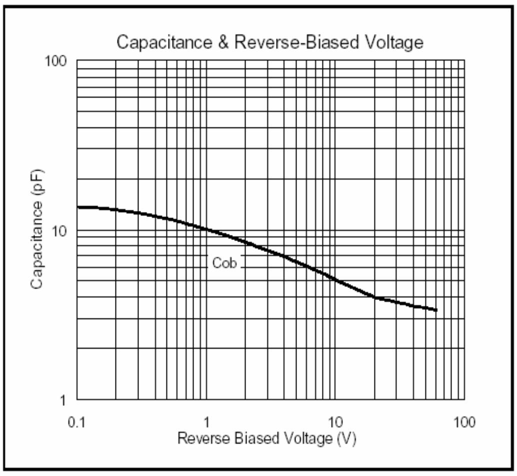
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

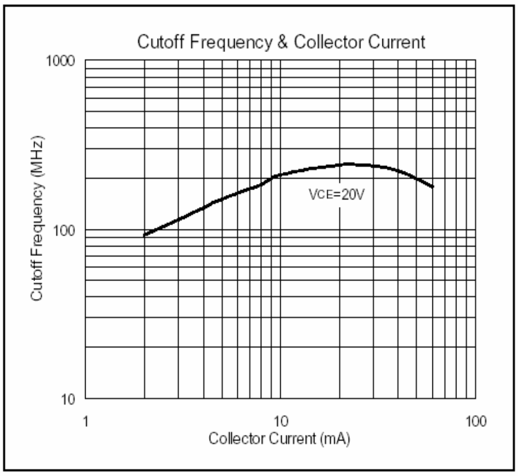
Characteristics Curve











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